

1200V 20A SiC Schottky Diode - SiS1200S20AS

Rev 1.0 30/10/23

Silicon Carbide Schottky Barrier Rectifier diode in bare die form

Features:

- Capable of high temperature operation >= 175°C
- High Frequency Operation
- High Surge Current Capability
- No Reverse Recovery / No Forward Recovery
- Positive Temperature Coefficient

Ordering Information:

The following part suffixes apply:

- No suffix MIL-STD-750 /2073 Visual Inspection
- "H" MIL-STD-750 /2073 Visual Inspection+ MIL-PRF-38534 Class H LAT
- "K" MIL-STD-750 /2073 Visual Inspection+ MIL-PRF-38534 Class K LAT

LAT = Lot Acceptance Test.

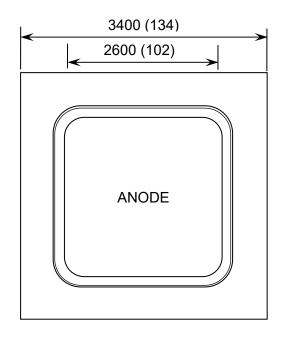
For further information on LAT process flows see below.

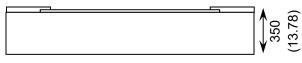
www.siliconsupplies.com\quality\bare-die-lot-qualification

Supply Formats:

- Default Die in Waffle Pack (100 per tray capacity)
- Sawn Wafer on Tape By specific request
- Unsawn Wafer By specific request
- With additional electrical selection By specific request

Die Dimensions in µm (mils)





CHIP BACKSIDE IS CATHODE

Mechanical Specification

Die Size (Unsawn)	3400 x 3400 134 x 134	μm mils	
Anode Pad Size	2600 x 2600 102 x 102	μm mils	
Die Thickness	350 (±20) 13.78 (0.79)	μm mils	
Top Metal Composition	Al 4µm		
Back Metal Composition	Ag 0.4μm		





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Absolute Maximum Ratings T_J = 25°C unless otherwise stated

PARAMETER	SYMBOL	VALUE	UNIT
Repetitive peak reverse voltage	V_{RRM}	1200	V
Surge peak reverse voltage	V_{RSM}	1200	V
DC Peak Blocking Voltage	V_{BR}	1200	V
Average forward rectified current	I _{F(AV)}	20	A
Repetitive Peak Forward Surge Current	I _{FRM}	86	A
Peak Single-Cycle Non-Repetitive Surge Current	I _{FSM}	162	А
Operating Junction temperature	TJ	-55 to 175	°C
Storage Temperature Range	T _{STG}	-65 to 175	°C

Electrical Characteristics T_J = 25°C unless otherwise stated

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Maximum instantaneous forward voltage ¹	V _{F1}	V _{RRM} = 1200V, I _{FM} = 20A	-	1.50	1.80	V
	V _{F2}	V _{RRM} = 1200V, I _{FM} = 20A, T _J = 175°C	-	2.20	3.00	
Maximum reverse leakage current ¹	I _{RM} @ V _{RM}	V _R = 1200V	-	1	25	μA
	IRM W VRM	V _R = 1200V, T _J = 175°C	-	10	150	μΛ
Junction Capacitance	Ст	$V_R = 0V$, $f = 1MHz$,	-	1620	-	pF
Reverse Recovery Charge	Q _C	$V_R = 800V$, $I_F = 20A$, $di/dt = 200A/\mu s$	-	124.89	-	nC
Capacitance Stored Energy	Ec	V _R = 800V	-	64.20	-	μJ

Pulse Width≤ 300µs, Duty Cycle ≤ 2.0%

Typical Characteristics T_J = 25°C

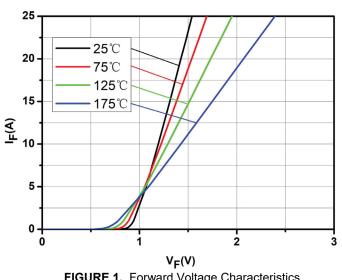


FIGURE 1. Forward Voltage Characteristics

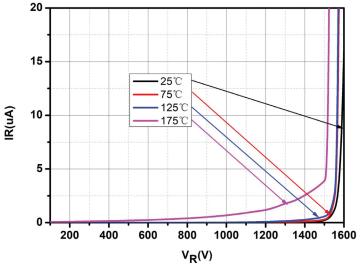


FIGURE 2. Reverse Characteristics





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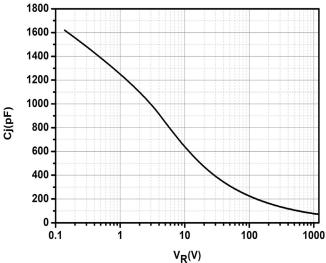


FIGURE 3. Capacitance Versus Reverse Voltage

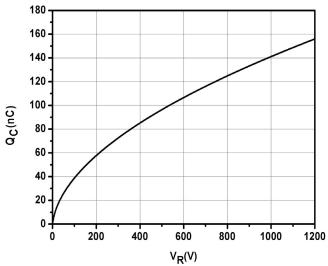


FIGURE 4. Total Capacitance Charge Versus Reverse Voltage

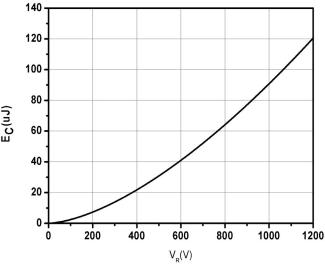


FIGURE 5. Capacitance Stored Energy

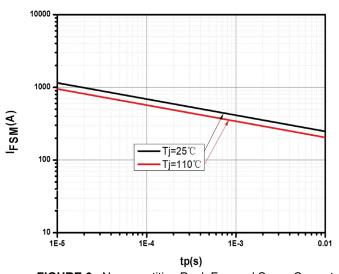


FIGURE 6. Non-repetitive Peak Forward Surge Current Versus Pulse Duration

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